

a first compound selected from the group consisting of zinc, indium, and tin and a second layer comprising said metal.

5. (Twice Amended) A light-emitting device according to Claim 1, wherein said second layer comprises a metal compound having said metal and a material selected from the group consisting of oxides, nitrides and oxide-nitrides.

14 (Amended) A light emitting device comprising:
a layer including an emission region;
an anode; and
a cathode, wherein said layer is disposed between said anode and said cathode, and
said anode has a visible light transmittance of 35 to 75%, a metal selected from the group consisting of Ni, Ru, Ir, Rh, Pt, Pd, Re, Ti, Zr, Nb, Mo, and W, and a dopant material selected from the group consisting of R_xNiO, R_xWO_y, and TiNb_xO_y, wherein R is selected from the group consisting of H, Li, Na, K, Rb, Cs, Cu, Ag, and Au.

15. (Amended) A light-emitting device according to Claim 1, where said second layer has a thickness in the range of 15 nm to 80 nm.

24. (New) A light-emitting device comprising a layer including an emission region and provided between an anode and a cathode wherein said anode has a visible light transmittance of 35 to 75%, a metal selected from the group consisting of Ni, Ru, Ir, Rh, Pt, Pd, Re, Ti, Zr, Nb, Mo, and W, and a first layer comprising a first compound selected from the group consisting of zinc, indium, and tin and a second layer comprising said metal, and wherein said second layer has a thickness that is greater than 20 nm and less than or equal to 80 nm.